# 74LV32 Quad 2-input OR gate Rev. 03 — 9 November 2007

**Product data sheet** 

### **General description** 1.

The 74LV32 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC32 and 74HCT32.

The 74LV32 provides a quad 2-input OR function.

### 2. **Features**

- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between V<sub>CC</sub> = 2.7 V and V<sub>CC</sub> = 3.6 V
- Typical output ground bounce < 0.8 V at  $V_{CC}$  = 3.3 V and  $T_{amb}$  = 25 °C
- Typical HIGH-level output voltage (V<sub>OH</sub>) undershoot: > 2 V at V<sub>CC</sub> = 3.3 V and  $T_{amb} = 25 \, ^{\circ}C$
- ESD protection:
  - ◆ HBM JESD22-A114E exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

# **Ordering information**

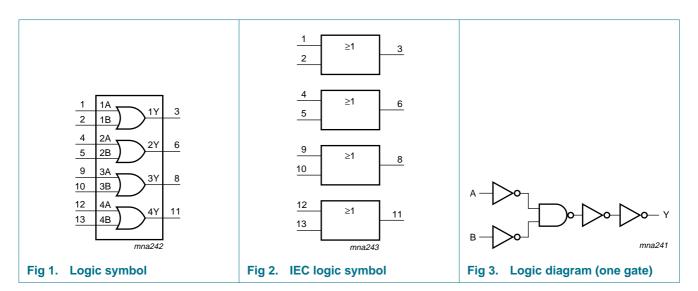
Table 1. **Ordering information** 

Type number	Package			
	Temperature range	Name	Description	Version
74LV32N	–40 °C to +125 °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1
74LV32D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74LV32DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1
74LV32PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74LV32BQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5\times3\times0.85$ mm	SOT762-1



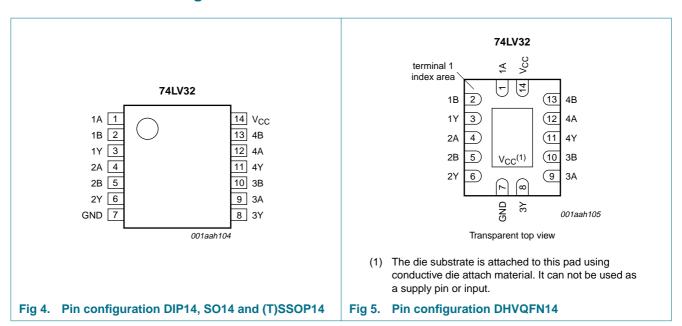
**Quad 2-input OR gate** 

# 4. Functional diagram



# 5. Pinning information

# 5.1 Pinning



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**Quad 2-input OR gate** 

# 5.2 Pin description

Table 2. Pin description

	-	
Symbol	Pin	Description
1A	1	data input
1B	2	data input
1Y	3	data output
2A	4	data input
2B	5	data input
2Y	6	data output
GND	7	ground (0 V)
3Y	8	data output
3A	9	data input
3B	10	data input
4Y	11	data output
4A	12	data input
4B	13	data input
$V_{CC}$	14	supply voltage

# 6. Functional description

Table 3. Function selection

 $H = HIGH \ voltage \ level; \ L = LOW \ voltage \ level; \ X = don't \ care$ 

Input	Output	
nA	nB	nY
Н	X	Н
X	Н	Н
L	L	L

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	[1] _	±20	mA
$I_{OK}$	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> _	±50	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	-	±25	mA
I <sub>CC</sub>	supply current		-	50	mA
$I_{GND}$	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C

**Quad 2-input OR gate** 

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$			
	DIP14 package		[2] -	750	mW
	SO14 package		<u>[3]</u> _	500	mW
	(T)SSOP14 package		<u>[4]</u> _	500	mW
	DHVQFN14 package		<u>[5]</u> _	500	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

# 8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CC}$	supply voltage[1]		1.0	3.3	5.5	V
$V_{I}$	input voltage		0	-	$V_{CC}$	V
V <sub>O</sub>	output voltage		0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.0 \text{ V to } 2.0 \text{ V}$	-	-	500	ns/V
		$V_{CC} = 2.0 \text{ V to } 2.7 \text{ V}$	-	-	200	ns/V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	-	100	ns/V
		$V_{CC} = 3.6 \text{ V to } 5.5 \text{ V}$	-	-	50	ns/V

<sup>[1]</sup> The static characteristics are guaranteed from  $V_{CC}$  = 1.2 V to  $V_{CC}$  = 5.5 V, but LV devices are guaranteed to function down to  $V_{CC}$  = 1.0 V (with input levels GND or  $V_{CC}$ ).

<sup>[2]</sup> P<sub>tot</sub> derates linearly with 12 mW/K above 70 °C.

<sup>[3]</sup> Ptot derates linearly with 8 mW/K above 70 °C.

<sup>[4]</sup> Ptot derates linearly with 5.5 mW/K above 60 °C.

<sup>[5]</sup> P<sub>tot</sub> derates linearly with 4.5 mW/K above 60 °C.

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# 9. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter Conditions		-40	°C to +8	35 °C	-40 °C to	Unit	
			Min	Typ[1]	Max	Min	Max	
$V_{IH}$	HIGH-level input voltage	V <sub>CC</sub> = 1.2 V	$V_{CC}$	0.6	-	V <sub>CC</sub>	-	V
		$V_{CC} = 2.0 \text{ V}$	1.4	-	-	1.4	-	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2.0	-	-	2.0	-	V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	$0.7V_{CC}$	-	-	0.7V <sub>CC</sub>	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 1.2 V	-	0.4	GND	-	GND	V
		V <sub>CC</sub> = 2.0 V	-	-	0.6	-	0.6	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	-	0.8	-	0.8	V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	$0.3V_{CC}$	-	$0.3V_{CC}$	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$						
		$I_O = -100 \mu A$ ; $V_{CC} = 1.2 \text{ V}$	-	1.2	-	-	-	V
		$I_O = -100 \mu A; V_{CC} = 2.0 V$	1.8	2.0	-	1.8	-	V
		$I_O = -100 \mu A; V_{CC} = 2.7 V$	2.5	2.7	-	2.5	-	V
		$I_O = -100 \mu A; V_{CC} = 3.0 \text{ V}$	2.8	3.0	-	2.8	-	V
		$I_O = -100 \mu A; V_{CC} = 4.5 V$	4.3	4.5	-	4.3	-	V
		$I_O = -6 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.4	2.82	-	2.2	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.6	4.2	-	3.5	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$						
		$I_O = 100 \mu A; V_{CC} = 1.2 V$	-	0	-	-	-	V
		$I_O = 100 \mu A; V_{CC} = 2.0 V$	-	0	0.2	-	0.2	V
		$I_O = 100 \mu A; V_{CC} = 2.7 V$	-	0	0.2	-	0.2	V
		$I_O = 100 \mu\text{A};  V_{CC} = 3.0 \text{V}$	-	0	0.2	-	0.2	V
		$I_O = 100 \mu A; V_{CC} = 4.5 V$	-	0	0.2	-	0.2	V
		$I_O = 6 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	0.25	0.40	-	0.50	V
		$I_O = 12 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.35	0.55	-	0.65	V
l <sub>l</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	1.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	20.0	-	40	μΑ
$\Delta I_{CC}$	additional supply current	per input; $V_I = V_{CC} - 0.6 \text{ V}$ ; $V_{CC} = 2.7 \text{ V}$ to 3.6 V	-	-	500	-	850	μΑ
Cı	input capacitance		-	3.5	-	-	-	pF

<sup>[1]</sup> Typical values are measured at  $T_{amb}$  = 25 °C.

**Quad 2-input OR gate** 

# 10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; For test circuit see Figure 7.

Symbol	Parameter	Conditions		-40	°C to +85	5 °C	–40 °C t	o +125 °C	Unit
				Min	Typ[1]	Max	Min	Max	
$t_{pd}$	propagation delay	nA, nB to nY; see Figure 6	[2]						
		V <sub>CC</sub> = 1.2 V		-	40	-	-	-	ns
		$V_{CC} = 2.0 \text{ V}$		-	14	22	-	28	ns
		V <sub>CC</sub> = 2.7 V		-	10	16	-	20	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V; } C_L = 15 \text{ pF}$	[3]	-	6.0	-	-	-	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	[3]	-	8.0	13	-	16	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V		-	-	10	-	13	ns
$C_{PD}$	power dissipation capacitance	$C_L$ = 50 pF; $f_i$ = 1 MHz; $V_I$ = GND to $V_{CC}$	<u>[4]</u>	-	16	-	-	-	pF

<sup>[1]</sup> All typical values are measured at  $T_{amb}$  = 25 °C.

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$$
 where:

 $f_i$  = input frequency in MHz,  $f_o$  = output frequency in MHz

 $C_L$  = output load capacitance in pF

V<sub>CC</sub> = supply voltage in V

N = number of inputs switching

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$  = sum of the outputs.

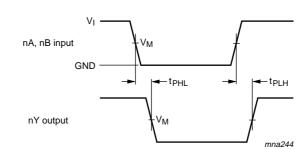
<sup>[2]</sup>  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

<sup>[3]</sup> Typical values are measured at nominal supply voltage ( $V_{CC} = 3.3 \text{ V}$ ).

<sup>[4]</sup>  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

**Quad 2-input OR gate** 

# 11. Waveforms



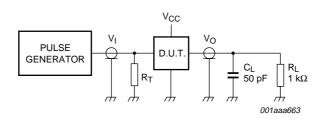
Measurement points are given in Table 8.

 $V_{\text{OL}}$  and  $V_{\text{OH}}$  are typical voltage output levels that occur with the output load.

Fig 6. The input (nA, nB) to output (nY) propagation delays

Table 8. Measurement points

Supply voltage	Input	Output
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>
< 2.7 V	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>
2.7 V to 3.6 V	1.5 V	1.5 V
≥ 4.5 V	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>



Test data is given in Table 9.

Definitions test circuit:

 $R_T$  = Termination resistance should be equal to output impedance  $Z_0$  of the pulse generator.

R<sub>L</sub> = Load resistance.

 $C_L$  = Load capacitance including jig and probe capacitance.

Fig 7. Load circuit for switching times

Table 9. Test data

Supply voltage	Input	
V <sub>CC</sub>	V <sub>I</sub>	$t_r$ , $t_f$
< 2.7 V	Vcc	≤ 2.5 ns
2.7 V to 3.6 V	2.7 V	≤ 2.5 ns
≥ 4.5 V	Vcc	≤ 2.5 ns

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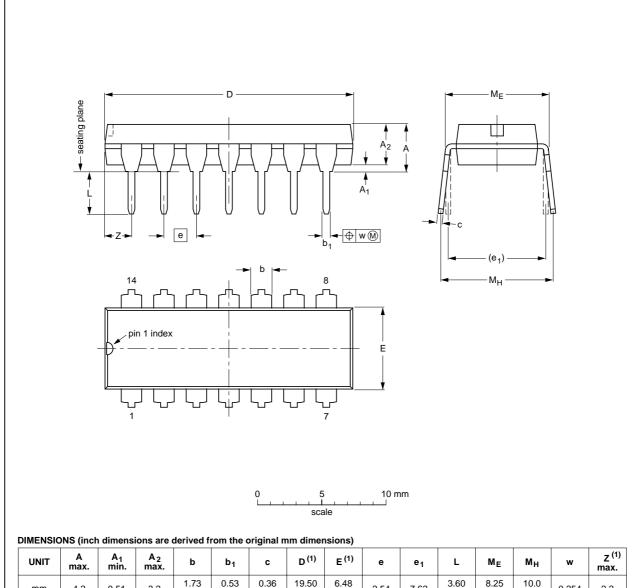
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**Quad 2-input OR gate** 

# 12. Package outline

## DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



	•					•									
UNIT	A max.	A <sub>1</sub> min.	A <sub>2</sub> max.	b	b <sub>1</sub>	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	e <sub>1</sub>	L	ME	Мн	w	Z <sup>(1)</sup> max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.02	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

### Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

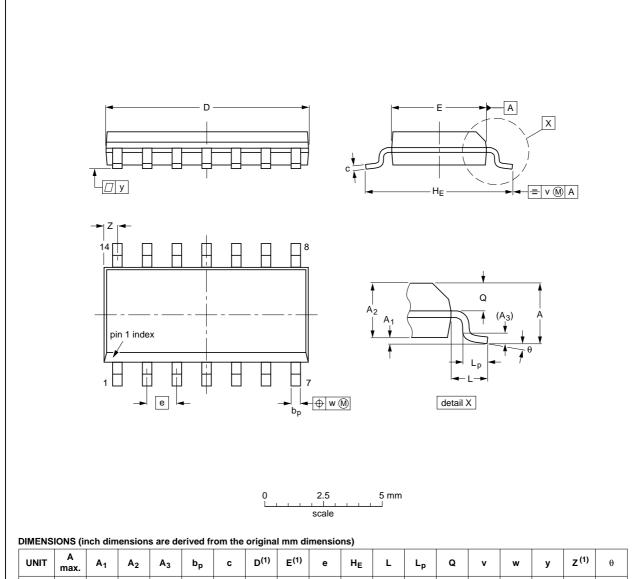
OUTLINE	OUTLINE REFERENCES	EUROPEAN	ISSUE DATE				
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT27-1	050G04	MO-001	SC-501-14			<del>99-12-27</del> 03-02-13	

Fig 8. Package outline SOT27-1 (DIP14)

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### SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	v	w	у	z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

### Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

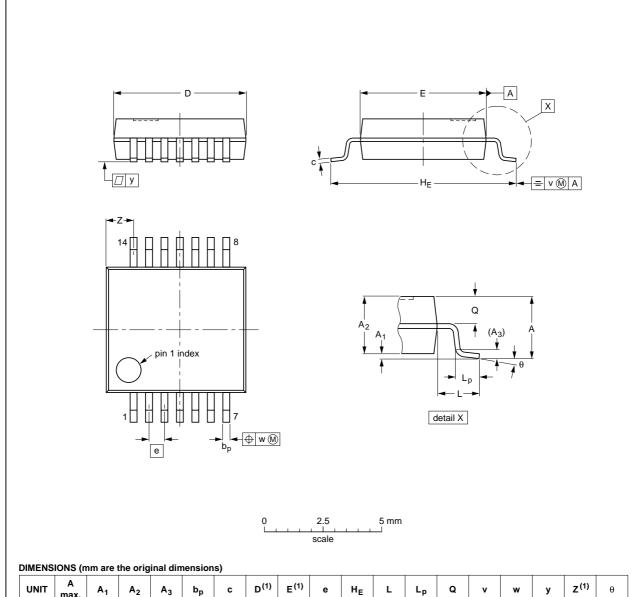
OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT108-1	076E06	MS-012				<del>99-12-27</del> 03-02-19	

Fig 9. Package outline SOT108-1 (SO14)

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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	v	w	у	z <sup>(1)</sup>	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

### Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

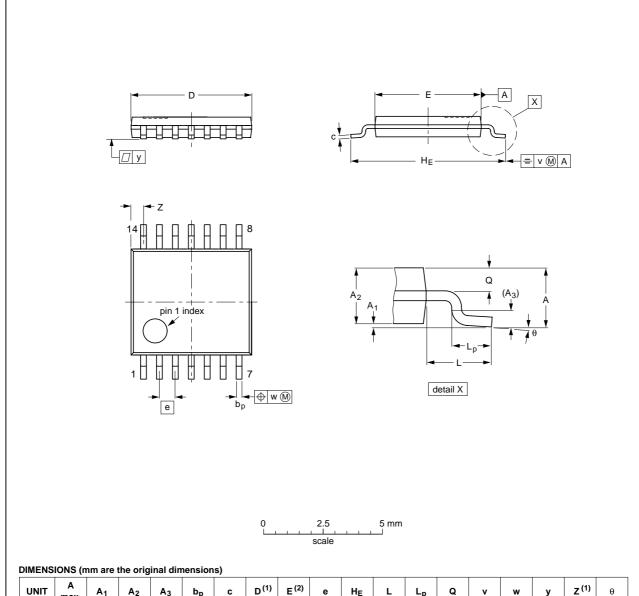
OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT337-1		MO-150				<del>-99-12-27</del> 03-02-19	

Fig 10. Package outline SOT337-1 (SSOP14)

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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	ø	v	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE	
SOT402-1		MO-153				<del>99-12-27</del> 03-02-18	

Fig 11. Package outline SOT402-1 (TSSOP14)

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

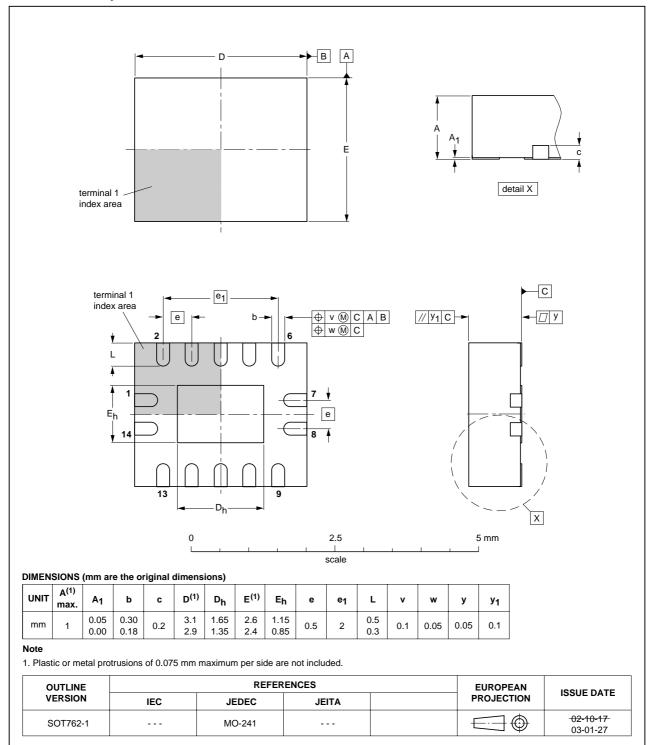


Fig 12. Package outline SOT762-1 (DHVQFN14)

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Quad 2-input OR gate

# 13. Abbreviations

### Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

# 14. Revision history

## Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes						
74LV32_3	20071109	Product data sheet	-	74LV32_2						
Modifications:	<ul> <li>The format of of NXP Semic</li> </ul>		designed to comply with	n the new identity guidelines						
	<ul> <li>Legal texts ha</li> </ul>	ve been adapted to the new	company name where	appropriate.						
	• Section 3: DH	VQFN14 package added.								
	<ul> <li>Section 8: derating values added for DHVQFN14 package.</li> </ul>									
	• Section 12: ou	Itline drawing added for DH\	/QFN14 package.							
74LV32_2	19980420	Product specification	-	74LV32_1						
74LV32_1	19970203	Product specification	-	-						

**Quad 2-input OR gate** 

# 15. Legal information

### 15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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For sales office addresses, send an email to: <a href="mailto:salesaddresses@nxp.com">salesaddresses@nxp.com</a>

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# **Quad 2-input OR gate**

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